

isc Silicon NPN Power Transistor

KSD526

DESCRIPTION

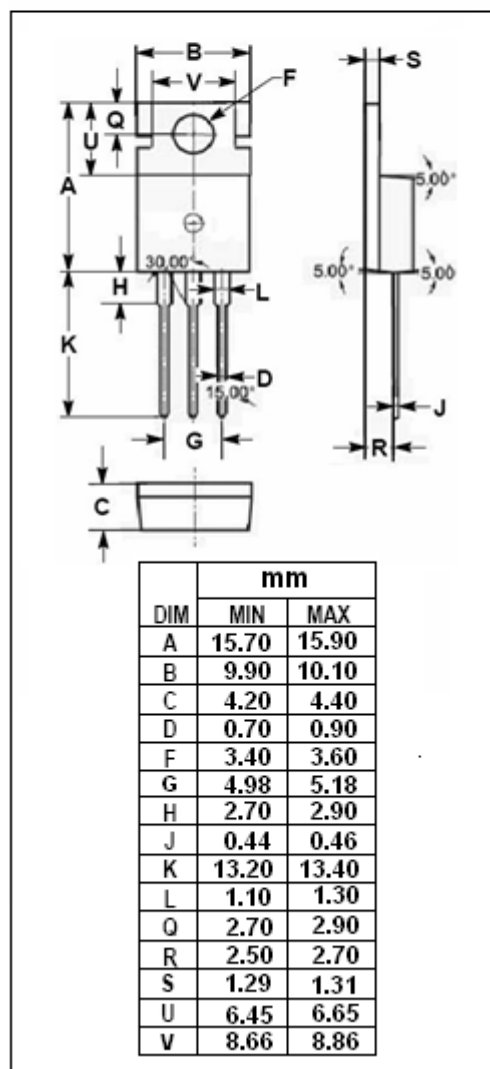
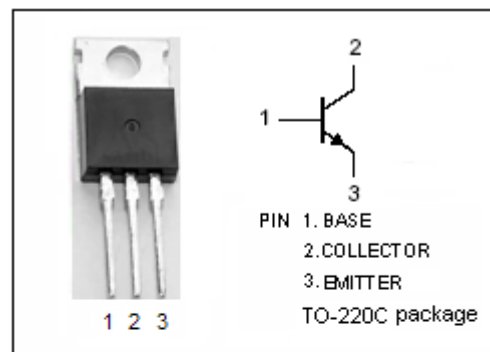
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 80V(\text{Min})$
- Good Linearity of h_{FE}
- Collector Power Dissipation-
: $P_C = 30W(\text{Max}) @ T_C = 25^\circ\text{C}$
- Complement to Type KSB596

APPLICATIONS

- Designed for power amplifier applications.
- Recommended for 20~25W high fidelity audio frequency amplifier output stage applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	80	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current-Continuous	4	A
I_B	Base Current-Continuous	0.4	A
P_C	Collector Power Dissipation @ $T_C=25^\circ\text{C}$	30	W
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature Range	-55~150	$^\circ\text{C}$



isc Silicon NPN Power Transistor**KSD526****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 50mA; I _B = 0	80			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = 10mA; I _C = 0	5			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 0.3A			1.5	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = 3A; V _{CE} = 5V			1.5	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 80V; I _E = 0			30	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			0.1	mA
h _{FE-1}	DC Current Gain	I _C = 0.5A; V _{CE} = 5V	40		240	
h _{FE-2}	DC Current Gain	I _C = 3A; V _{CE} = 5V	15			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1.0MHz		90		pF
f _T	Current-Gain—Bandwidth Product	I _C = 0.5A; V _{CE} = 5V		8		MHz

◆ h_{FE-1} Classifications

R	O	Y
40-80	70-140	120-240